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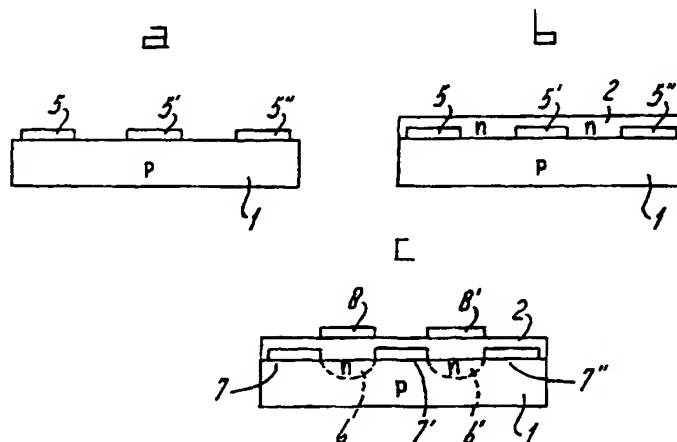
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(54) Title: **METHOD FOR THE PRODUCTION OF A SEMICONDUCTOR DEVICE**



(57) Abstract: The invention relates to a method for making a semiconductor device having a pattern of highly doped regions (6, 6') located some distance apart in a semiconductor substrate (1) and regions (7, 7', 7'') of low doping located between the highly doped regions (6, 6'). According to the invention a diffusion barrier material (5, 5', 5'') is applied to the semiconductor substrate at the location of the regions of low doping by means of imprinting with the barrier material in the pattern of the regions of low doping. The doping material is applied after or before imprinting with the barrier material so that the highly doped regions are formed essentially between the barrier material in the substrate. With the method according to the invention the doping concentrations in the regions of low doping and in the highly doped regions can be freely adjusted independently of one another so that a relatively low surface resistance can be obtained for the highly doped regions to give good conducting contact with the metalisation and a high surface resistance can be achieved in the regions of low doping.

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